

N-Channel 100 V (D-S) MOSFET

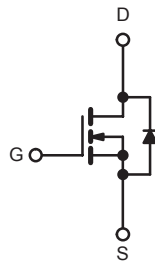
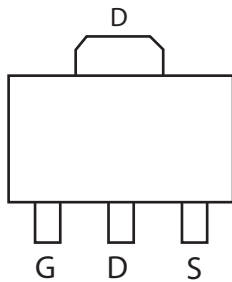
MOSFET PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω) Typ.	I _D (A) ^a	Q _g (Typ.)
100	0.102 at V _{GS} = 10 V	4.2	2.9 nC
	0.120 at V _{GS} = 6 V	3.8	
	0.125 at V _{GS} = 4.5 V	3.6	

FEATURES

- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested

APPLICATIONS

- DC/DC Converters / Boost Converters
- Load Switch
- LED Backlighting in LCD TVs
- Power Management for Mobile Computing



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	A
		T _C = 70 °C	
		T _A = 25 °C	
		T _A = 70 °C	
Pulsed Drain Current (t = 300 μs)	I _{DM}	15	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	
Single Pulse Avalanche Current	I _{AS}	3	mJ
Single Pulse Avalanche Energy	E _{AS}	0.45	
Maximum Power Dissipation	P _D	T _C = 25 °C	W
		T _C = 70 °C	
		T _A = 25 °C	
		T _A = 70 °C	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	75	100	°C/W	
Maximum Junction-to-Foot (Drain)	R _{thJF}	40	50		

Notes:

- Based on T_C = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under steady state conditions is 166 °C/W.

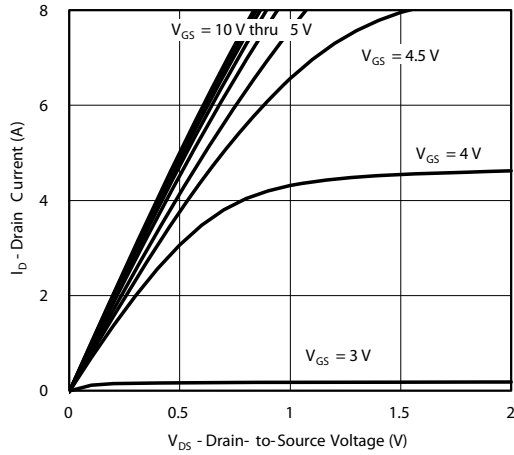
MOSFET SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	100			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		59		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 4.8		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.2		3	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	5			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 2 A		0.102		□
		V _{GS} = 6 V, I _D = 1 A		0.120		
		V _{GS} = 4.5 V, I _D = 1 A		0.125		
Forward Transconductance ^a	g _{fs}	V _{DS} = 20 V, I _D = 2 A		5		S
Dynamic^b						
Input Capacitance	C _{iss}	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz		196		pF
Output Capacitance	C _{oss}			67		
Reverse Transfer Capacitance	C _{rss}			14		
Total Gate Charge	Q _g	V _{DS} = 50 V, V _{GS} = 10 V, I _D = 2.2 A		5.2	10.4	nC
				2.9	5.8	
Gate-Source Charge	Q _{gs}	V _{DS} = 50 V, V _{GS} = 4.5 V, I _D = 2.2 A		1		
Gate-Drain Charge	Q _{gd}			1.4		
Gate Resistance	R _g	f = 1 MHz	0.9	4.3	8.6	□
Turn-On Delay Time	t _{d(on)}	V _{DD} = 50 V, R _L = 27.7 Ω I _D = 1.8 A, V _{GEN} = 4.5 V, R _g = 1 Ω		40	60	ns
Rise Time	t _r			68	102	
Turn-Off Delay Time	t _{d(off)}			14	21	
Fall Time	t _f			20	30	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 50 V, R _L = 27.7 Ω I _D = 1.8 A, V _{GEN} = 10 V, R _g = 1 Ω		8	16	
Rise Time	t _r			10	20	
Turn-Off Delay Time	t _{d(off)}			10	20	
Fall Time	t _f			7	14	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 2.1	A
Pulse Diode Forward Current ^a	I _{SM}				- 8	
Body Diode Voltage	V _{SD}	I _S = 1.8 A		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 1.8 A, dI/dt = 100 A/μs, T _J = 25 °C		23	35	ns
Body Diode Reverse Recovery Charge	Q _{rr}			21	32	nC
Reverse Recovery Fall Time	t _a			17		ns
Reverse Recovery Rise Time	t _b			6		

Notes:

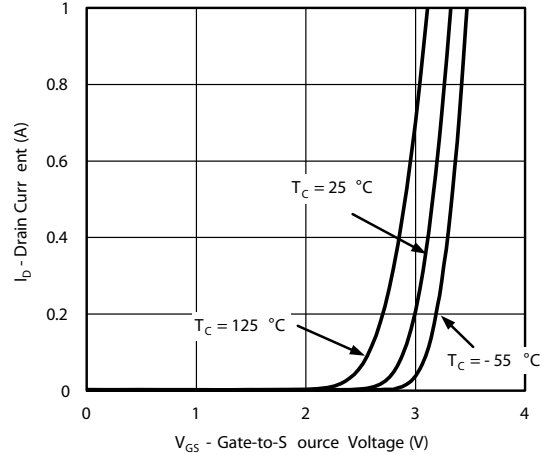
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

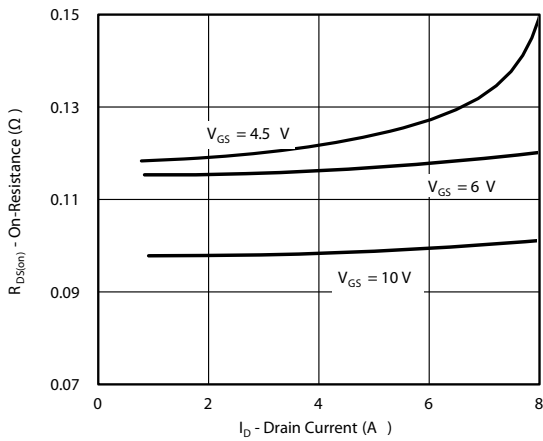
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



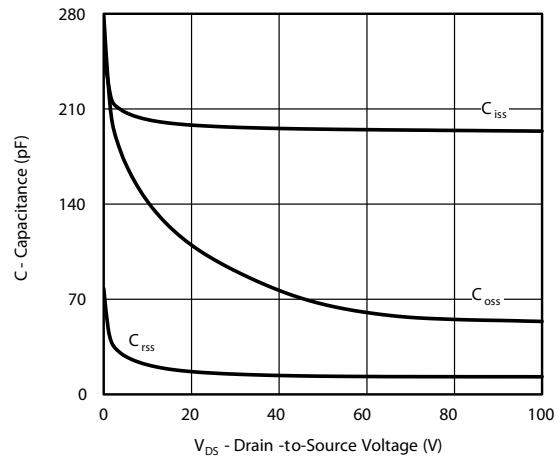
Output Characteristics



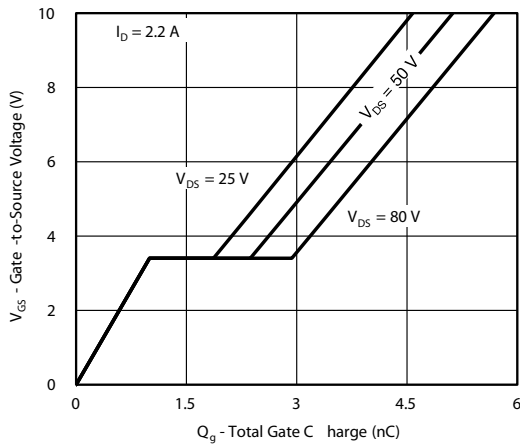
Transfer Characteristics



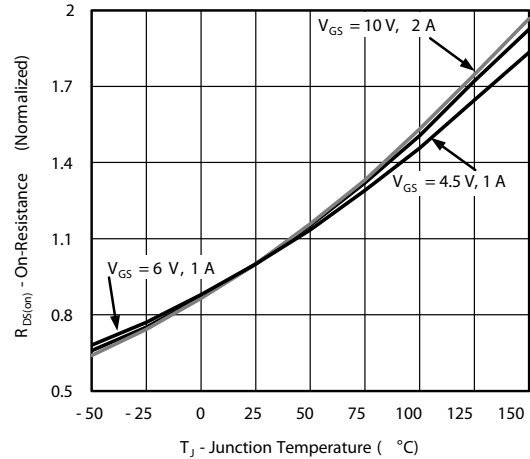
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

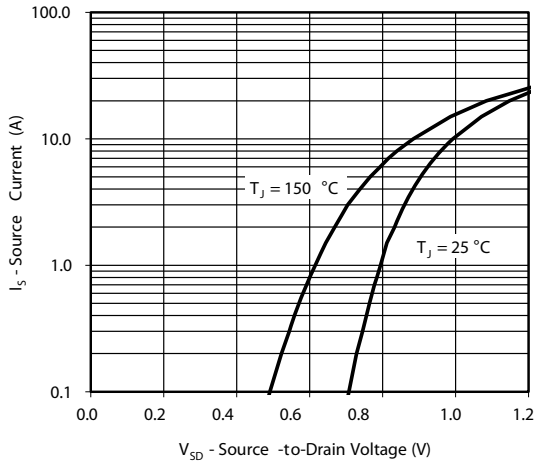


Gate Charge

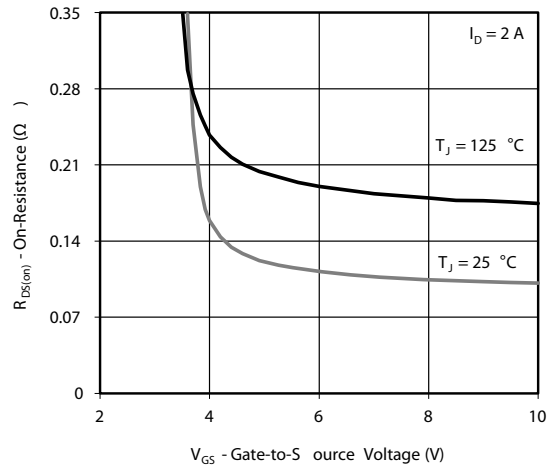


On-Resistance vs. Junction Temperature

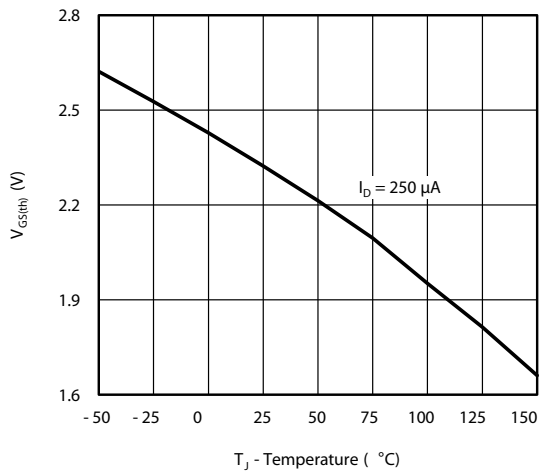
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



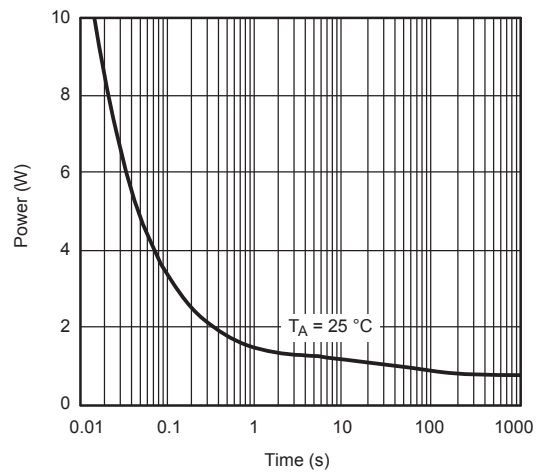
Source-Drain Diode Forward Voltage



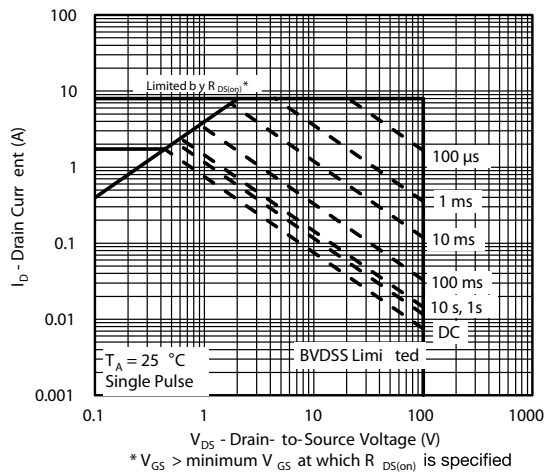
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



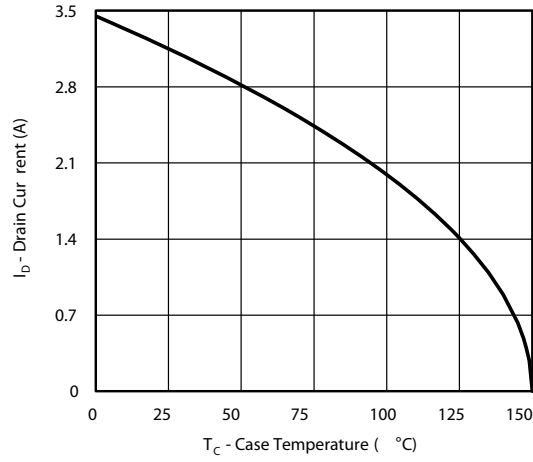
Single Pulse Power



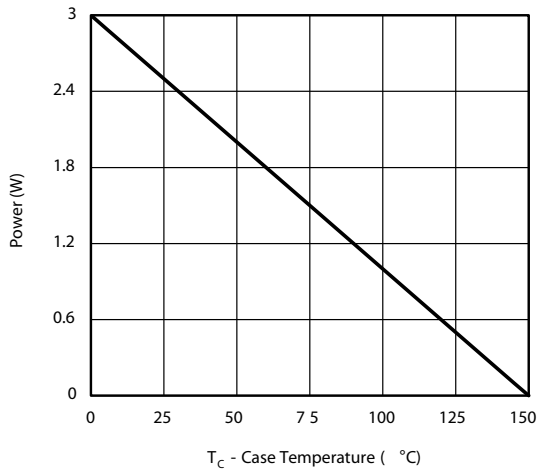
Safe Operating Area

TYPICAL CHARACTERISTICS

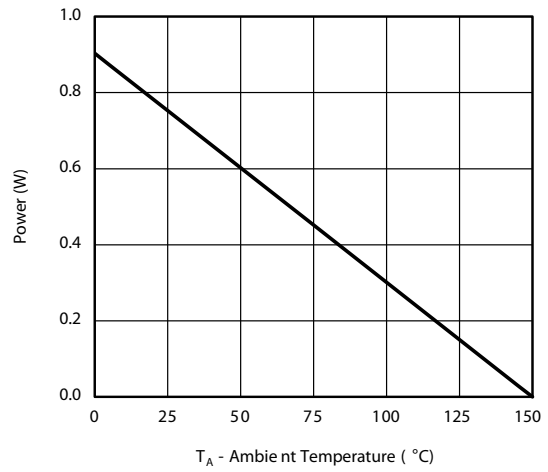
(25 °C, unless otherwise noted)



Current Derating*



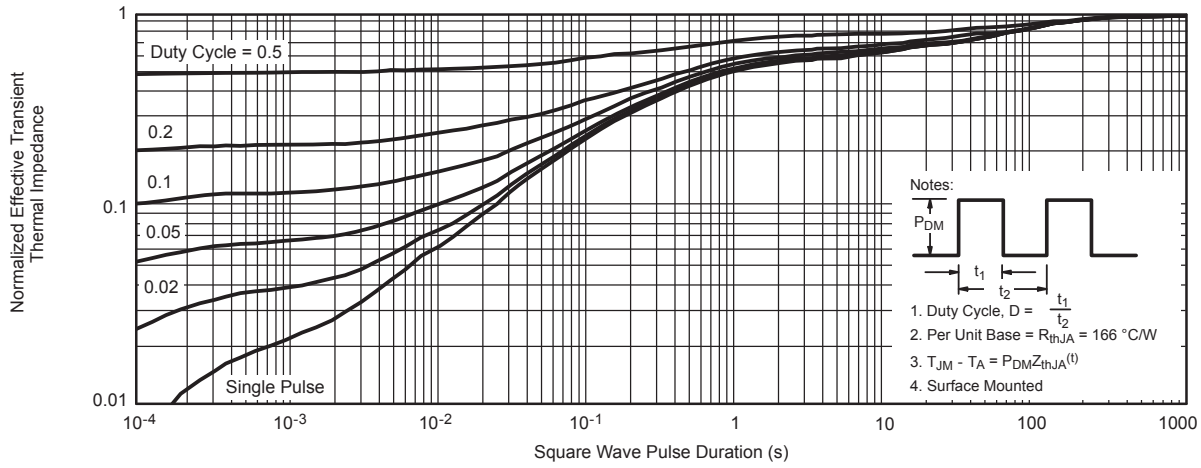
Power, Junction-to-Foot



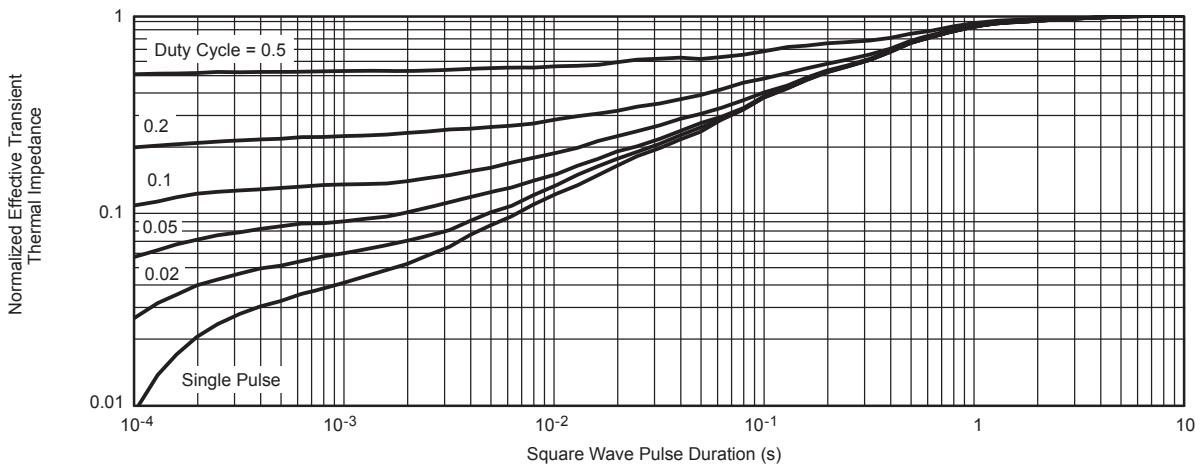
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max.)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

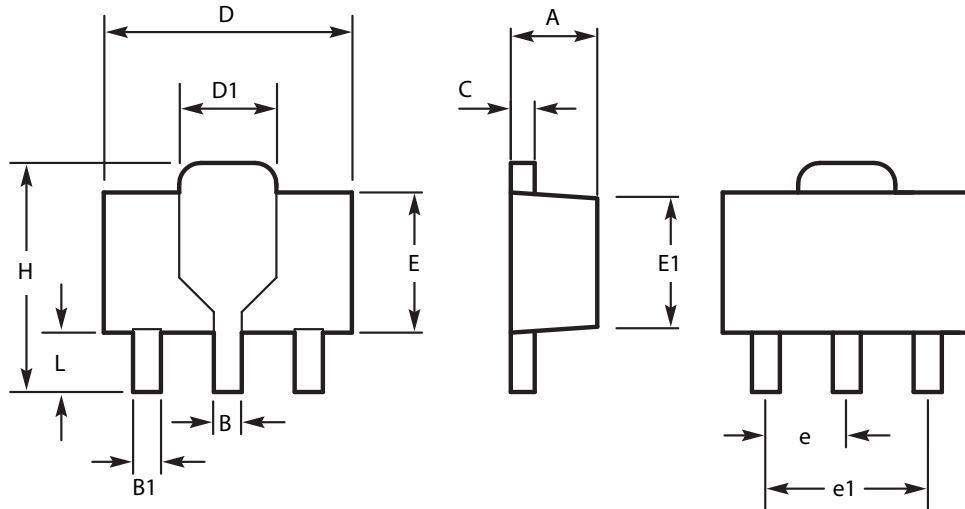


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Package outline - SOT89



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	E	2.29	2.60	0.090	0.102
B	0.44	0.56	0.017	0.022	E	12.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	e	1.50 BSC		0.059 BSC	
C	0.35	0.44	0.014	0.017	e1	3.00 BSC		0.118 BSC	
D	4.40	4.60	0.173	0.181	H	3.94	4.25	0.155	0.167
D1	1.62	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches